

**MOSFET chip DMOST056**

**Description**

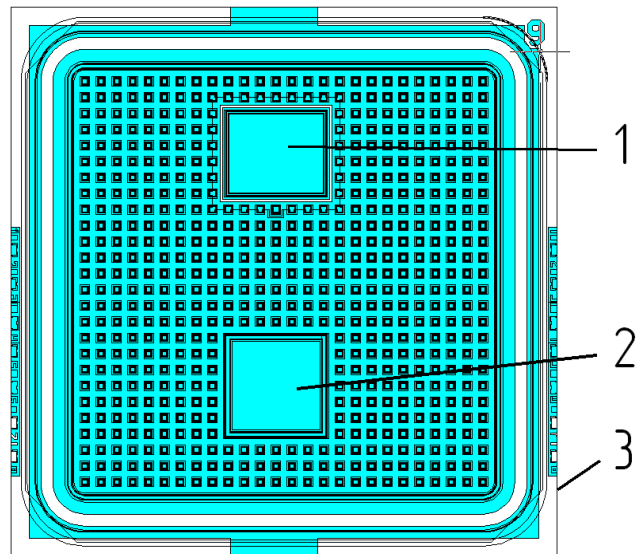
MOSFET chip with induced channel (normally-off) DMOST056 is designed to be used in hybrid microchips and packaged field-effect transistors.

**Features**

- Chip size – 1.37 x1.37 mm
- Chip thickness – 0.42±0.02 mm
- Contact pads size:  
Gate – 0.248 x0.208 mm  
Source – 0.221 x 0.221 mm
- Metallization: top – AlSi,  
bottom – CrAu for bonding on conductive adhesive

**Absolute Maximum Ratings**

Maximum Temperature	
Storage Temperature	- 55 °C to 100 °C
Operating Junction Temperature	- 45 °C to 85 °C
Maximum Voltage	
Drain-to-Source Voltage	60 V
Gate-to-Source Voltage	±20 V



- 1 - Gate
- 2 - Source
- 3 - Drain

**Electrical Characteristics (T<sub>A</sub> = 25 °C)**

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-to-Source ON-State Resistance	R <sub>DS</sub>	Ohm			1.1	V <sub>GS</sub> = 5 V, I <sub>D</sub> = 300 mA
Gate Leakage Current	I <sub>LEAK.G</sub>	μA			0.1	V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V
Drain Leakage Current	I <sub>LEAK.D</sub>	μA			1	V <sub>GS</sub> = 0 V, U <sub>D</sub> = 60 V
LED Constant Forward Voltage (drain <sup>-</sup> , source <sup>+</sup> )	V <sub>SD</sub>	V			0.85	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 120 mA